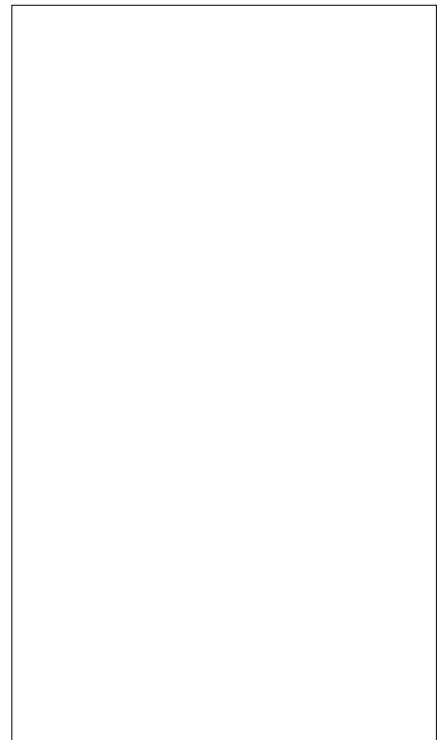




ACJT04H-1000SW 4A TRIAC

Rev.A.1.0

The ACJT04H-1000SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT04H-1000SW embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. Package TO-251 is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	1000	V

$V_a V_a$

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	1000	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	1000	V
RMS on-state current ($T_c = 98^\circ C$)	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^\circ C$)	I_{TSM}	40	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^\circ C$)		44	
I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$)	I^2t	8	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100Hz$, $T_j=125^\circ C$)	di/dt	50	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	3.25	kV
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(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	30	mA
				45	
I_H	$I_T=100mA$		MAX.	25	mA
dV/dt	$V_D=670V$ Gate Open $T_j=125$		MIN.	250	V/ μs
(dI/dt) _c	(dV/dt) _c =10V/ μs , $T_j=125$		MIN.	3.5	A/ms
t_{on}	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	2.5	μs
t_{off}				25	
V_{CL}	$I_{CL}=0.1mA t_p=1ms$		MIN.	1050	V

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=5.6A t_p=380\mu s$	$T_j=25$	1.6	V
V_{TO}	Threshold voltage	$T_j=125$	0.9	V
R_D	Dynamic resistance	$T_j=125$	80	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	8	μA
I_{RRM}		$T_j=125$	0.4	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	4.5	W
$R_{th(j-a)}$	junction to ambient (AC)	120	W

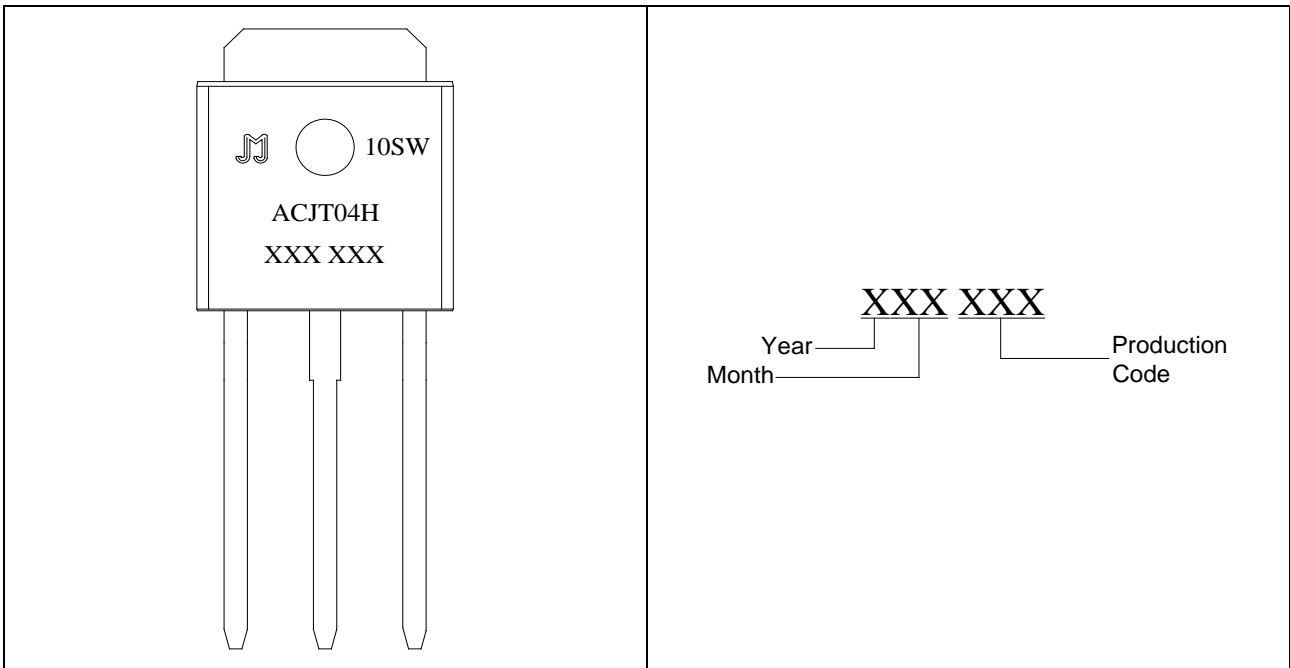
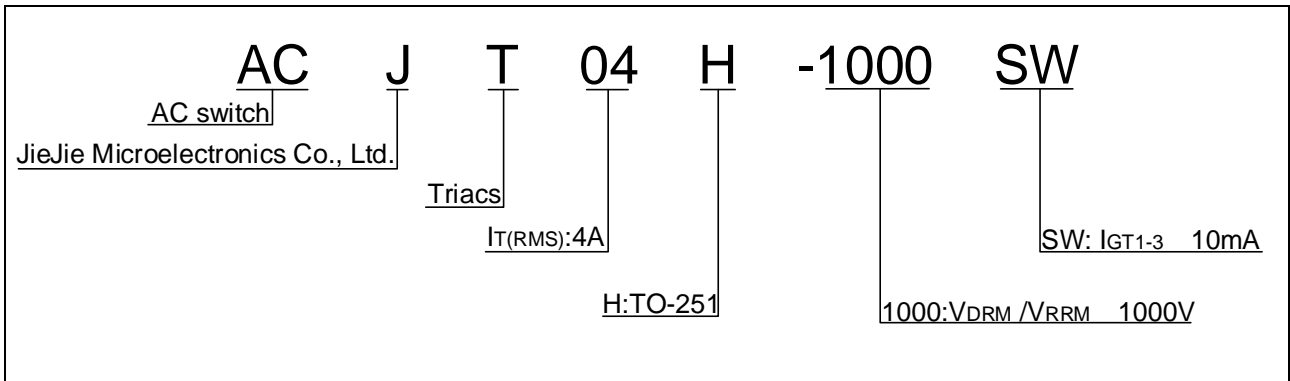


FIG.1 Maximum power dissipation versus RMS on-state current

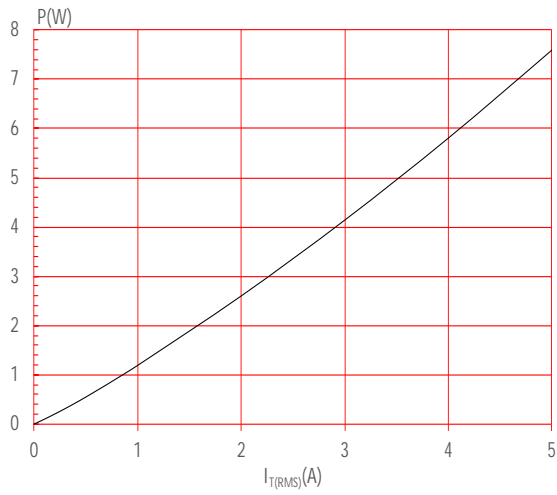


FIG.2: RMS on-state current versus case temperature

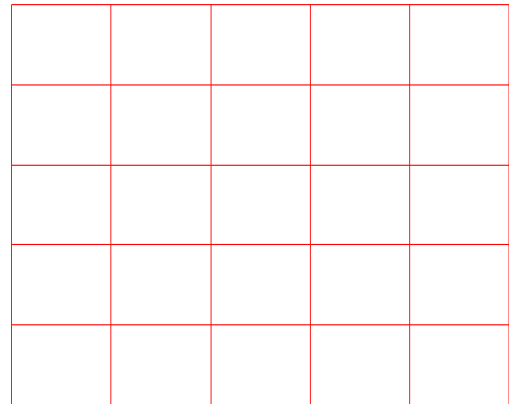
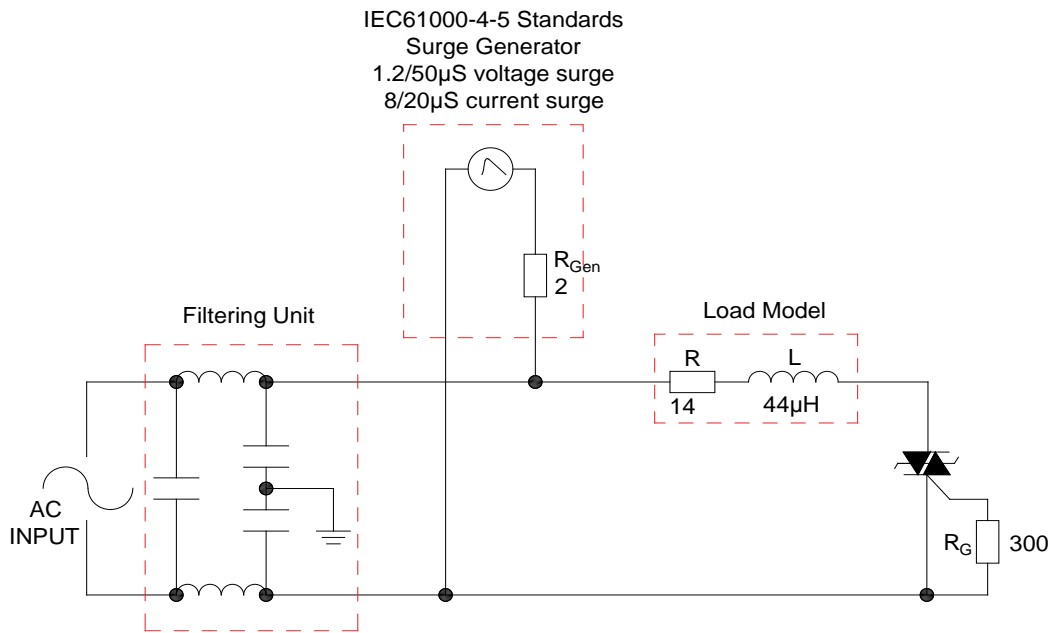


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

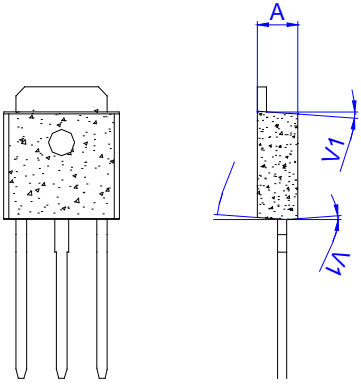


Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT04H-1000SW	1000	10	TO-251	80	Tube

Document Revision History

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated



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